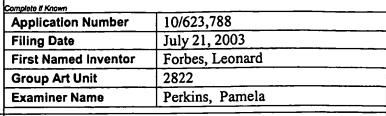
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INFORMATION DISCLOSURE
STATEMENT BY APPLICANT

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Sheet 1 of 2

Attomey Docket No: 1303.109US1

	WE WAS DEED TO SHEET					
		US PAT	ENT DOCUMENTS			
Examiner initial *	USP Document Number	Publication Date	Name of Patentee or Applicant of cited Document	Filing Date If Appropriate		
PEP	US-20020185686A1	12/12/2002	Christiansen, S. H., et al.	04/03/2002		
1	US-20030131782A1	07/17/2003	Geusic, Joseph E., et al.	01/17/2002		
	US-20030181018A1	09/25/2003	Geusic, Joseph E., et al.	03/25/2002		
	US-20040176483A1	09/09/2004	Geusic, Joseph E.	03/05/2003		
	US-20050070036A1	03/31/2005	Geusic, Joseph E., et al.	05/16/2001		
	US-20050105869A1	05/19/2005	Forbes, L., et al.	12/07/2004		
	US-20050250274A1	11/10/2005	Forbes, L., et al.	06/27/2005		
	US-20050285139A1	12/29/2005	Forbes, L.	08/24/2005		
	US-20060001094A1	01/05/2006	Forbes, L.	08/29/2005		
	US-20060011982A1	01/19/2006	Forbes, L.	08/24/2005		
	US-20060097281A1	05/11/2006	Forbes, L.	12/23/2005		
	US-5,679,475	10/21/1997	Yamagata, K., et al.	01/04/1995		
	US-6,855,649	02/15/2005	Christiansen, Silke, et al.	11/19/2002		
	US-6,900,094	05/31/2005	Hammond, R., et al.	06/14/2002		
	US-6,987,037	01/17/2006	Forbes, L.	05/07/2003		
	US-7,008,854	03/07/2006	Forbes, L.	05/21/2003		
	US-7,023,051	04/04/2006	Forbes, L.	08/31/2004		
1/	US-7,041,575	05/09/2006	Forbes, L.	04/29/2003		
A	US-7,045,874	05/16/2006	Forbes, L.	08/31/2004		
PEP	US-7,054,532	05/30/2006	Forbes, L., et al.	12/07/2004		

FOREIGN PATENT DOCUMENTS				
Examiner Initials*	Foreign Document No	Publication Date	Name of Patentee or Applicant of cited Document	L ₃

	OTHE	R DOCUMENTS NON PATENT LITERATURE DOCUMENTS	
Examiner Initials*	Cite No 1	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T²
PEP	:	ANG, KAH W., "Enhanced performance in 50 nm N-MOSFETs with silicon- carbon source/drain regions", <u>IEEE International Electron Devices Meeting</u> , 2004. IEDM Technical Digest., (Dec., 2004),1069-1071	
PEP		FORBES, K Y., "Non-Volatile Memory Device with Tensile Strained Silicon Layer", U.S. Application No. 11/260,339 (client ref no 05-0753 - Leffert file), 26 pgs	
PEP		GHANI, T., "A 90nm High Volume Manufacturing Logic Technology Featuring Novel 45nm Gate Length Strained Silicon CMOS Transistors", <u>Technical Digest IEEE International Electron Devices Meeting</u> , (Dec., 2003),978-980	
PEP		GOTO, K., "Technology Booster using Strain-Enhancing Laminated SiN (SELS) for 65nm Node Hp MPUs", IEDM Technical Digest. IEEE International Electron Devices Meeting, (Dec., 2004),209-212	

EXAMINER

/Pamela Perkins/

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PTO/SB/06A(10-01)
Approved for use through 10/31/2002, QMB 651-0031

Substitute for form 1449A/PTO	Under the Peperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid QMG control number. Complete if Known		
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary)	Application Number	10/623,788 July 21, 2003	
	Filing Date		
	First Named Inventor	Forbes, Leonard	
	Group Art Unit	2822	
	Examiner Name	Perkins, Pamela	
Sheet 2 of 2	Attorney Docket No: 1	1303.109US1	

	OTHE	R DOCUMENTS NON PATENT LITERATURE DOCUMENTS	
Examiner Initials*	Cite No 1	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	L
PEP		KOMODA, T., "Mobility Improvement for 45nm Node by Combination of Optimized Stress Control and Channel Orientation Design", IEEE International Electron Devices Meeting, 2004. IEDM Technical Digest., (Dec., 2004),217-220	
PEP		MAIKAP, S., "Package-strain-enhanced device and circuit performance", <u>IEEE International Electron Devices Meeting</u> , 2004. IEDM Technical Digest., (Dec., 2004),233-236	
PEP		PIDIN, S., "A Novel Strain Enhanced CMOS Architecture Using Selectively Deposited High Tensile and High Compressive Silicon Nitride Films", <u>IEEE International Electron Devices Meeting</u> , 2004. IEDM Technical Digest., (Dec., 2004),213-216	
PEP		THOMPSON, S. E., "Key Differences For Process-induced Uniaxial vs. Substrate-induced Biaxial Stressed Si and Ge Channel MOSFETs", IEEE International Electron Devices Meeting, 2004. IEDM Technical Digest., (Dec., 2004),221-224	